NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI VMB70-12S** is Designed for

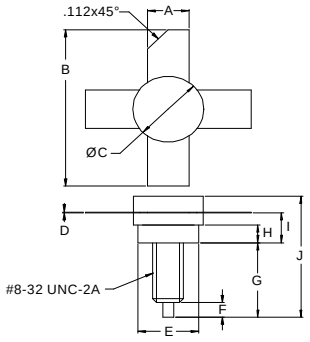
FEATURES:

-
-
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	12 A
V_{CBO}	36 V
V_{CEO}	18 V
V_{EBO}	3.5 V
P_{DISS}	183 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.05 °C/W

PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10746

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 50 mA	36			V
BV_{CES}	I_C = 100 mA	36			V
BV_{CEO}	I_C = 50 mA	18			V
BV_{EBO}	I_E = 10 mA	4.0			V
I_{CES}	V_E = 12.5 V			10	mA
h_{FE}	V_{CE} = 5.0 V I_C =5.0 A	10		---	---
C_{OB}	V_{CB} = 12.5 V f = 1.0 MHz			270	pF
P_G	V_{CC} = 12.5 V P_{OUT} = 70 W f = 88 MHz	7.0			dB
η_C			60		%

Specifications are subject to change without notice.